



**THE DATASHEET OF
SGC6489Z**



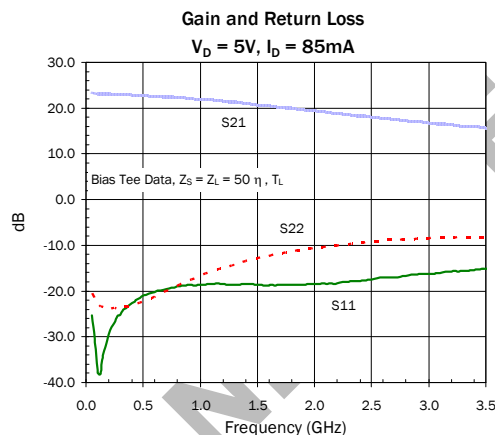


Product Description

RFMD's SGC-6489Z is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 5V supply, the SGC-6489Z does not require a dropping resistor as compared to traditional Darlington amplifiers. The SGC-6489Z product is designed for high linearity 5V gain block applications that require small size and minimal external components. It is internally matched to 50Ω.

Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- InP HBT
- RF MEMS
- LDMOS



Features

- Single Supply Operation: 5V at $I_D = 85\text{mA}$
- No Dropping Resistor Required
- Patented Self Bias Circuitry
- Gain = 19.5dBm at 1950MHz
- P1dB = 19.2dBm at 1950MHz
- IP3 = 32.8dBm at 1950MHz
- Robust 1000V ESD, Class 1C HBM

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

| Parameter | Specification | | | Unit | Condition |
|------------------------------------|---------------|------|------|------|------------------|
| | Min. | Typ. | Max. | | |
| Small Signal Gain | 20.7 | 22.2 | 23.7 | dB | 850MHz |
| | 18.0 | 19.5 | 21.0 | dB | 1950MHz |
| | | 18.3 | | dB | 2400MHz |
| Output Power at 1dB Compression | | 20.6 | | dBm | 850MHz |
| | 17.7 | 19.2 | | dBm | 1950MHz |
| | | 18.4 | | dBm | 2400MHz |
| Output Third Order Intercept Point | | 34.1 | | dBm | 850MHz |
| | 30.8 | 32.8 | | dBm | 1950MHz |
| | | 31.4 | | dBm | 2400MHz |
| Input Return Loss | 14 | 18 | | dB | 1950MHz |
| Output Return Loss | 8 | 11 | | dB | 1950MHz |
| Noise Figure | | 2.4 | 3.4 | dB | 1930MHz |
| Device Operating Voltage | | 5 | | V | |
| Device Operating Current | 70 | 82 | 94 | mA | |
| Thermal Resistance | | 70 | | °C/W | junction to lead |

Test Conditions: $V_D = 5.0\text{V}$, $I_D = 82\text{mA}$, $T_L = 25^\circ\text{C}$, OIP3 Tone Spacing = 1MHz, Bias Tee Data, $Z_S = Z_L = 50\Omega$, P_{OUT} per tone = 0dBm

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---------------------------------------|------------|------|
| Max Device Current (I_{CE}) | 100 | mA |
| Max Device Voltage (V_{CE}) | 7 | V |
| Max RF Input Power* (See Note) | 3 | dBm |
| Max Junction Temperature (T_J) | +150 | °C |
| Operating Temperature Range (T_L) | -40 to +85 | °C |
| Max Storage Temperature | +150 | °C |
| ESD Rating - Human Body Model (HBM) | Class 1C | |
| Moisture Sensitivity Level | MSL 2 | |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

*Note: Load condition $Z_L = 50\Omega$

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

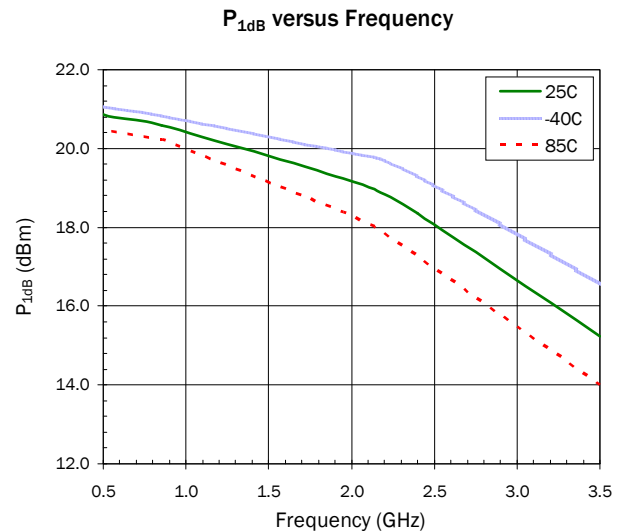
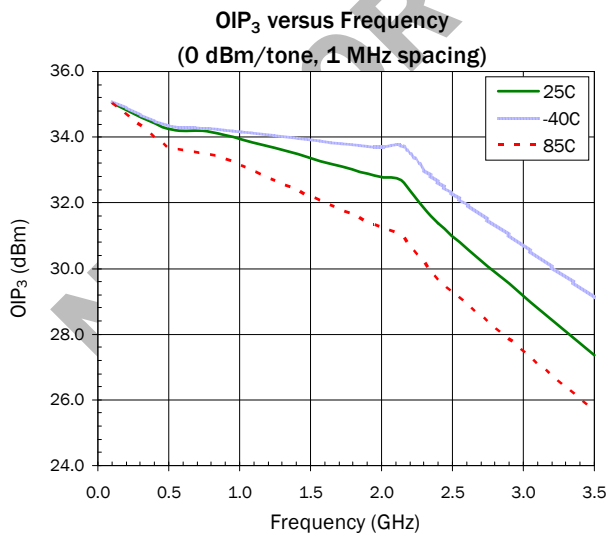
$$I_D V_D < (T_J - T_L) / R_{TH, J - I} \text{ and } T_L = T_{LEAD}$$

Typical RF Performance at Key Operating Frequencies (Bias Tee Data)

| Parameter | Unit | 100 | 500 | 850 | 1950 | 2140 | 2400 | 3500 |
|--|------|------|------|------|------|------|------|------|
| | | MHz | MHz | MHz | MHz | MHz | MHz | MHz |
| Small Signal Gain (G) | dB | 23.1 | 22.7 | 22.2 | 19.5 | 19.0 | 18.3 | 15.7 |
| Output Third Order Intercept Point (OIP_3) | dBm | 35.1 | 34.3 | 34.1 | 32.8 | 32.7 | 31.4 | 27.4 |
| Output Power at 1dB Compression (P_{1dB}) | dBm | 21.8 | 20.9 | 20.6 | 19.2 | 19.0 | 18.4 | 15.2 |
| input Return Loss (IRL) | dB | 37.0 | 22.0 | 19.0 | 18.0 | 18.0 | 17.0 | 16.0 |
| Output Return Loss (ORL) | dB | 23.0 | 22.0 | 19.0 | 11.0 | 11.0 | 10.0 | 8.0 |
| Reverse Isolation (S_{12}) | dB | 25.0 | 25.0 | 26.0 | 25.0 | 25.0 | 24.0 | 22.0 |
| Noise Figure (NF) | dB | 1.8 | 2.0 | 2.1 | 2.4 | 2.4 | 2.5 | 2.9 |

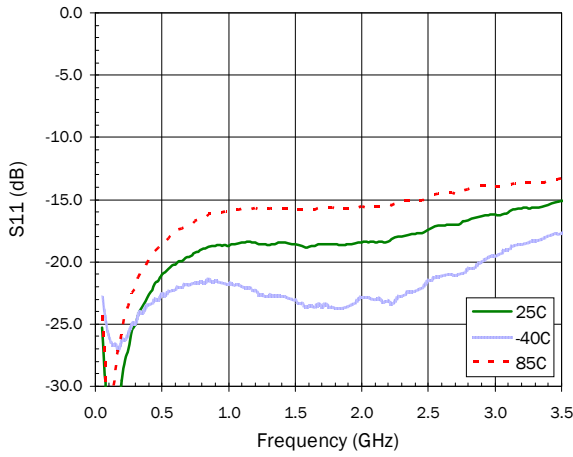
Test Conditions: $V_D = 5V$ $I_D = 85mA$ OIP_3 Tone Spacing = 1MHz, P_{OUT} per tone = 0dBm $T_L = 25^\circ C$ $Z_S = Z_L = 50\Omega$

Typical Performance with Bias Tees, $V_D = 5V$, $I_D = 82mA$

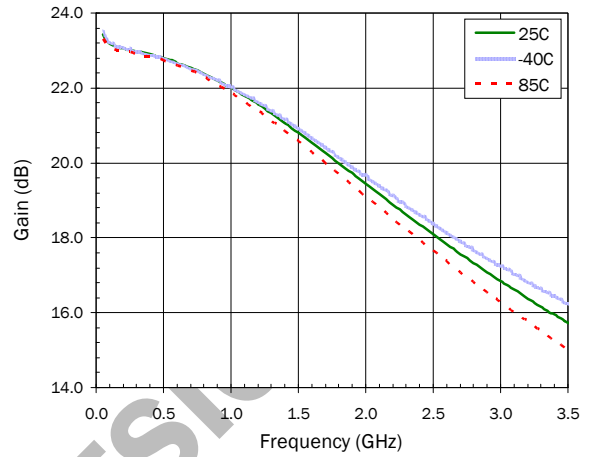


Typical Performance with Bias Tees, $V_D = 5V$, $I_D = 82mA$

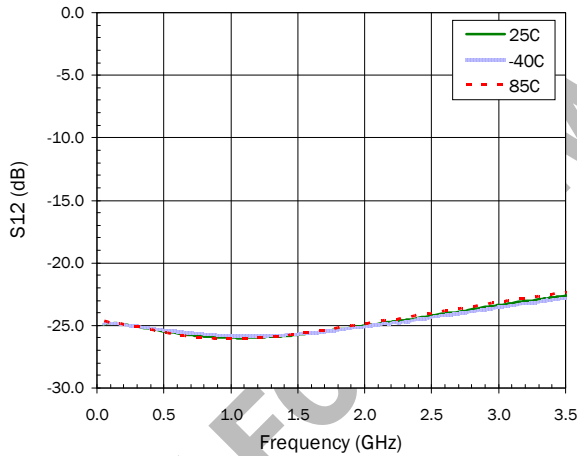
S11 versus Frequency



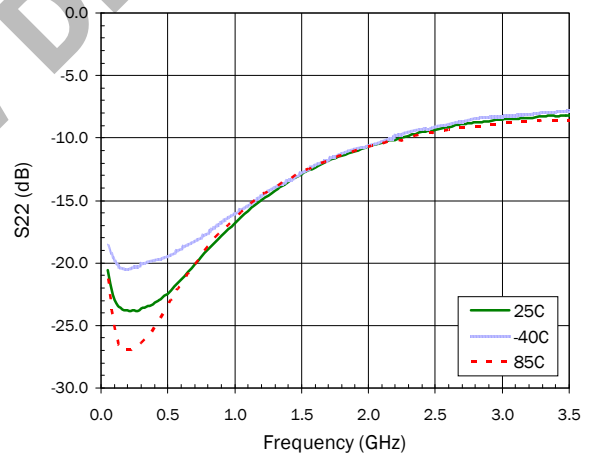
S21 versus Frequency



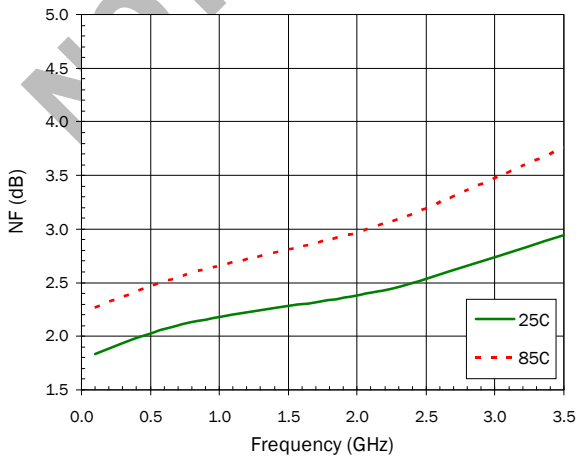
S12 versus Frequency



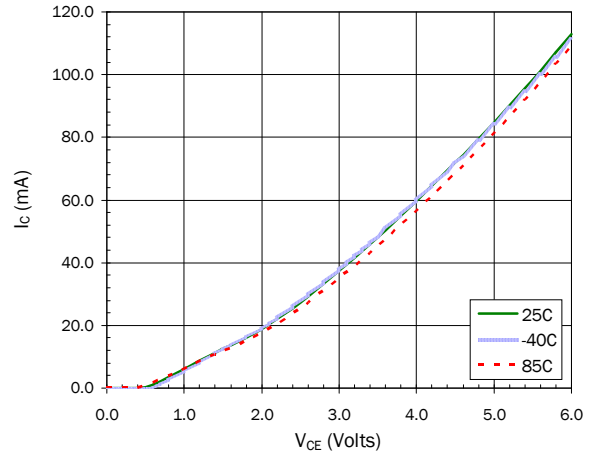
S22 versus Frequency



NF versus Frequency



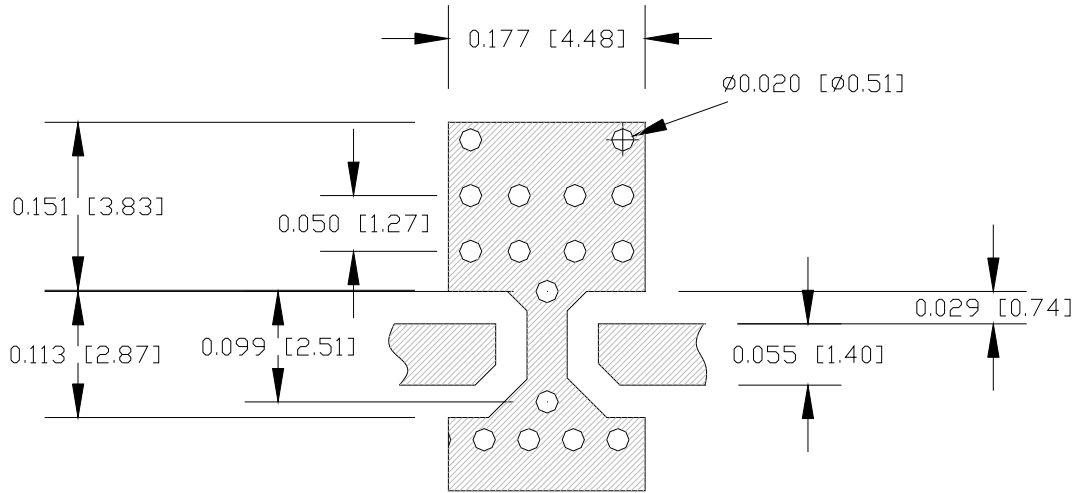
DCIV versus Temperature



| Pin | Function | Description |
|------|-------------------|---|
| 1 | RF IN | RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation. |
| 2, 4 | GND | Connection to ground. Use via holes as close to the device ground leads as possible to reduce ground inductance and achieve optimum RF performance. |
| 3 | RF OUT/ DCBIAS | RF output and bias pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation. |

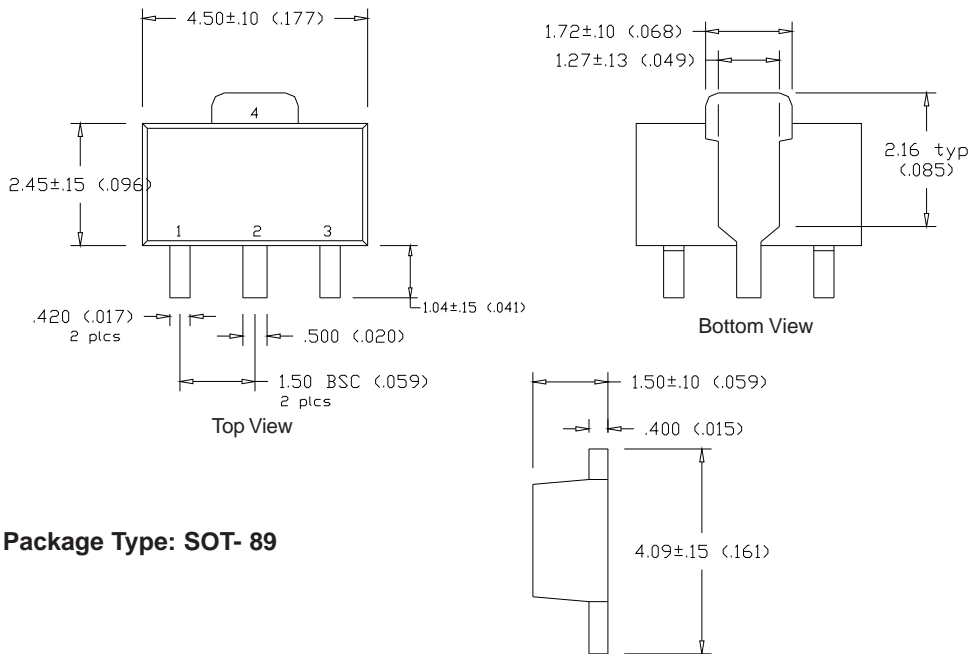
Suggested PCB Pad Layout

Dimensions in inches (millimeters)



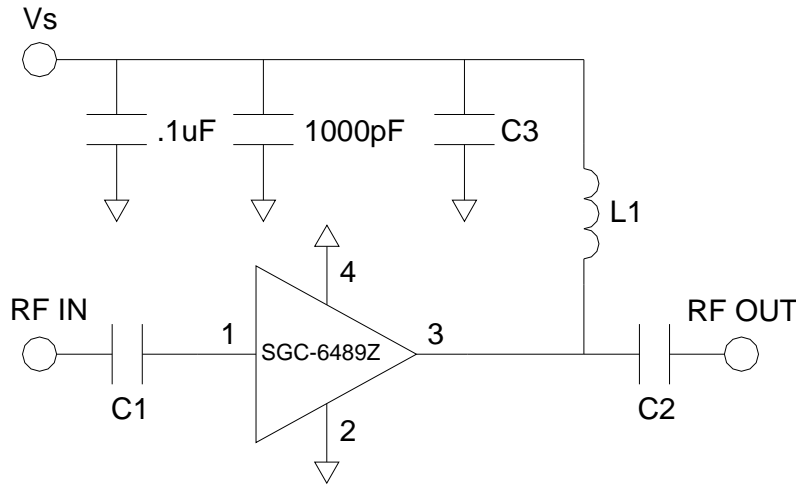
Package Drawing

Dimensions in inches (millimeters)



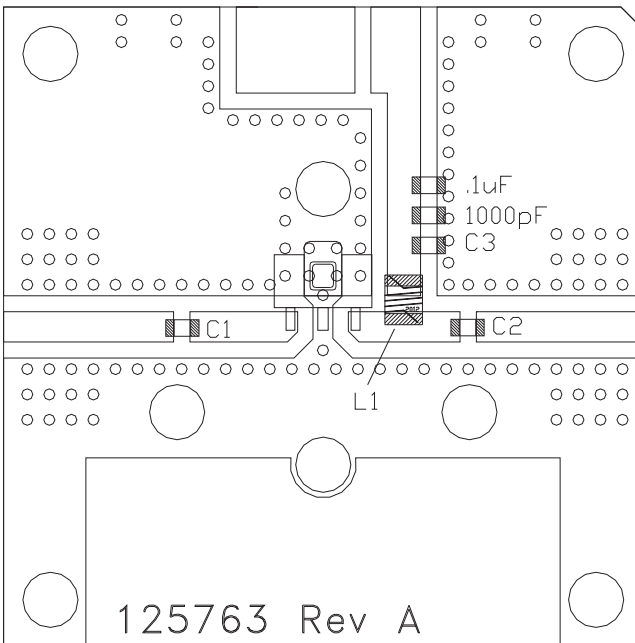
Package Type: SOT- 89

Application Schematic



| Reference Designator | 500 - 2100 MHz |
|----------------------|----------------|
| C1 | 43pF |
| C2 | 43pF |
| C3 | 100pF |
| L1 | 48nH 0805HQ CC |

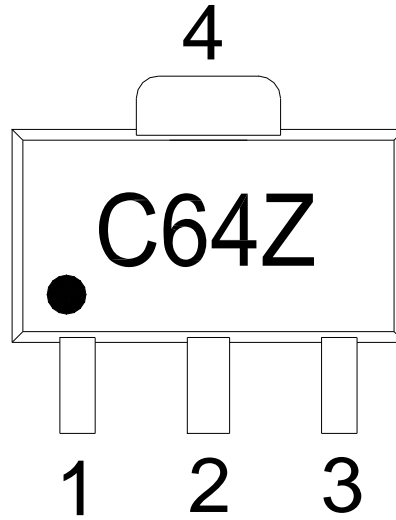
Evaluation Board



Mounting Instructions

1. Solder the copper pad on the backside of the device package to the ground plane.
2. Use a large ground pad area with many plated through-holes as shown.
3. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Part Identification



Alternate marking "SGC6489Z" on line one with Trace Code on line two.

Ordering Information

| Part Number | Package / Lead Composition | Reel Size | Devices / Reel |
|----------------|-------------------------------|-----------|----------------|
| SGC-6489Z | Lead Free, RoHS Compliant | 13" | 3000 |
| SGC-6489Z-EVB1 | 100-1000 MHz Evaluation Board | N/A | N/A |
| SGC-6489Z-EVB2 | 500-2100 MHz Evaluation Board | N/A | N/A |

NOT A

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